



# STD8NM60ND, STF8NM60ND STP8NM60ND, STU8NM60ND

N-channel 600 V, 0.59  $\Omega$  , 7 A, FDmesh™ II Power MOSFET  
TO-220, TO-220FP, IPAK, DPAK

## Features

Type	V <sub>DSS</sub> (@T <sub>jmax</sub> )	R <sub>DS(on)</sub> max	I <sub>D</sub>
STD8NM60ND	650 V	< 0.70 $\Omega$	7 A
STF8NM60ND	650 V	< 0.70 $\Omega$	7 A
STP8NM60ND	650 V	< 0.70 $\Omega$	7 A <sup>(1)</sup>
STU8NM60ND	650 V	< 0.70 $\Omega$	7 A

1. Limited only by maximum temperature allowed

- The worldwide best R<sub>DS(on)</sub>\* area amongst the fast recovery diode devices
- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance
- Extremely high dv/dt and avalanche capabilities

## Application

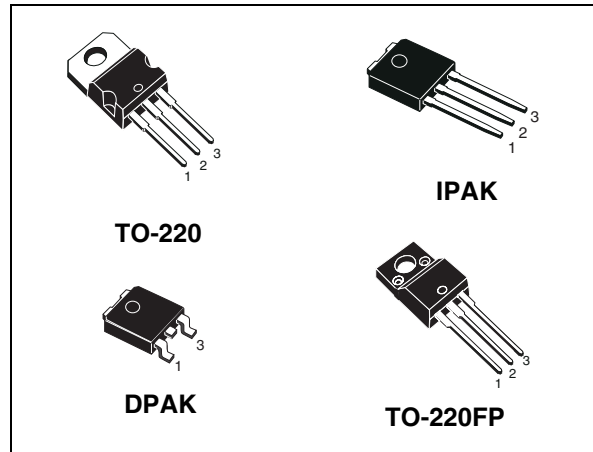
- Switching applications

## Description

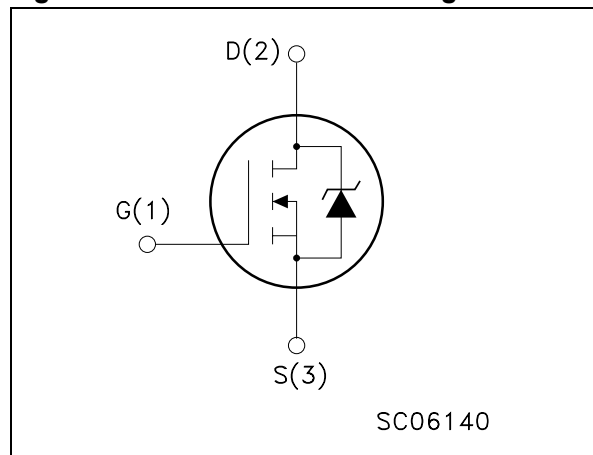
The FDmesh™ II series belongs to the second generation of MDmesh™ technology. This revolutionary Power MOSFET associates a new vertical structure to the company's strip layout and associates all advantages of reduced on-resistance and fast switching with an intrinsic fast-recovery body diode. Strongly recommended for bridge topologies, in ZVS phase-shift converters.

**Table 1. Device summary**

Order codes	Marking	Package	Packaging
STD8NM60ND	8NM60ND	DPAK	Tape and reel
STF8NM60ND	8NM60ND	TO-220FP	Tube
STP8NM60ND	8NM60ND	TO-220	Tube
STU8NM60ND	8NM60ND	IPAK	Tube



**Figure 1. Internal schematic diagram**



# Contents

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value				Unit
		TO-220	DPAK	IPAK	TO-220FP	
$V_{DS}$	Drain-source voltage ( $V_{GS} = 0$ )	600				V
$V_{GS}$	Gate-source voltage	$\pm 30$				V
$I_D$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	7		7 <sup>(1)</sup>		A
$I_D$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	4.4		4.4 <sup>(1)</sup>		A
$I_{DM}^{(2)}$	Drain current (pulsed)	28		28 <sup>(1)</sup>		A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	70		25		W
$V_{ISO}$	Insulation withstand voltage (RMS) from all three leads to external heat sink ( $t = 1\text{ s}; T_C = 25\text{ }^\circ\text{C}$ )	2500				V
$dv/dt^{(3)}$	Peak diode recovery voltage slope	40				V/ns
$T_{stg}$	Storage temperature	-55 to 150				$^\circ\text{C}$
$T_j$	Max. operating junction temperature	150				$^\circ\text{C}$

- Limited only by maximum temperature allowed
- Pulse width limited by safe operating area
- $I_{SD} \leq 7\text{ A}$ ,  $di/dt \leq 400\text{ A}/\mu\text{s}$ ,  $V_{DD} = 80\% V_{(BR)DSS}$

**Table 3. Thermal data**

Symbol	Parameter	Value				Unit
		TO-220	DPAK	IPAK	TO-220FP	
$R_{thj-case}$	Thermal resistance junction-case	1.79			5	$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-amb	62.5		100	62.5	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}$	Thermal resistance junction-pcb		50			$^\circ\text{C}/\text{W}$
$T_l$	Maximum lead temperature for soldering purpose	300				$^\circ\text{C}$

**Table 4. Avalanche characteristics**

Symbol	Parameter	Max value	Unit
$I_{AS}$	Avalanche current, repetitive or not-repetitive (pulse width limited by $T_j$ max)	2.5	A
$E_{AS}$	Single pulse avalanche energy (starting $T_j = 25\text{ }^\circ\text{C}$ , $I_D = I_{AS}$ , $V_{DD} = 50\text{ V}$ )	200	mJ

## 2 Electrical characteristics

( $T_{CASE} = 25\text{ °C}$  unless otherwise specified)

**Table 5. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$ , $V_{GS} = 0$	600			V
$dv/dt^{(1)}$	Drain-source voltage slope	$V_{DD} = 480\text{ V}$ , $I_D = 7\text{ A}$ , $V_{GS} = 10\text{ V}$		45		V/ns
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = \text{Max rating}$ , $V_{DS} = \text{Max rating}$ , $T_c = 125\text{ °C}$			1 100	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$ , $I_D = 3.5\text{ A}$		0.59	0.70	$\Omega$

1. Characteristics value at turn off on inductive load

**Table 6. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 15\text{ V}$ , $I_D = 5\text{ A}$		7.5		S
$C_{iss}$ $C_{oss}$ $C_{rss}$	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 50\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0$		560 37 4		pF pF pF
$C_{oss\text{ eq.}}^{(2)}$	Equivalent output capacitance	$V_{GS} = 0$ , $V_{DS} = 0\text{ to }480\text{ V}$		90		pF
$R_G$	Gate input resistance	$f = 1\text{ MHz}$ Gate DC Bias = 0 Test Signal Level = 20 mV Open Drain		6		$\Omega$
$Q_g$ $Q_{gs}$ $Q_{gd}$	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 480\text{ V}$ , $I_D = 7\text{ A}$ $V_{GS} = 10\text{ V}$ <i>Figure 19</i>		22 4 13		nC nC nC

1. Pulsed: pulse duration = 300 $\mu\text{s}$ , duty cycle 1.5%

2.  $C_{oss\text{ eq.}}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$

**Table 7. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300\text{ V}$ , $I_D = 7\text{ A}$ ,		9		ns
$t_r$	Rise time	$R_G = 4.7\ \Omega$ , $V_{GS} = 10\text{ V}$		22		ns
$t_{d(off)}$	Turn-off delay time	<a href="#">Figure 18</a> ,		37		ns
$t_f$	Fall time	<a href="#">Figure 23</a>		22		ns

**Table 8. Source drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current				7	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				28	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 7\text{ A}$ , $V_{GS} = 0$			1.3	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 7\text{ A}$ , $di/dt = 100$		120		ns
$Q_{rr}$	Reverse recovery charge	$A/\mu s$ , $V_{DD} = 30\text{ V}$ ,		0.49		$\mu C$
$I_{RRM}$	Reverse recovery current	<a href="#">Figure 20</a>		8		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 7\text{ A}$ ,		170		ns
$Q_{rr}$	Reverse recovery charge	$di/dt = 100\text{ A}/\mu s$ ,		0.75		$\mu C$
$I_{RRM}$	Reverse recovery current	$V_{DD} = 30\text{ V}$ , $T_j = 150^\circ C$		9		A

1. Pulse width limited by safe operating area

2. Pulsed: pulse duration = 300  $\mu s$ , duty cycle 1.5%

## 2.1 Electrical characteristics

Figure 2. Safe operating area for TO-220

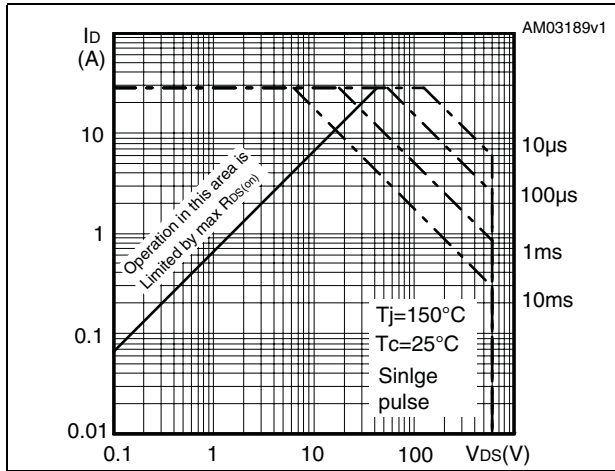


Figure 3. Thermal impedance for TO-220

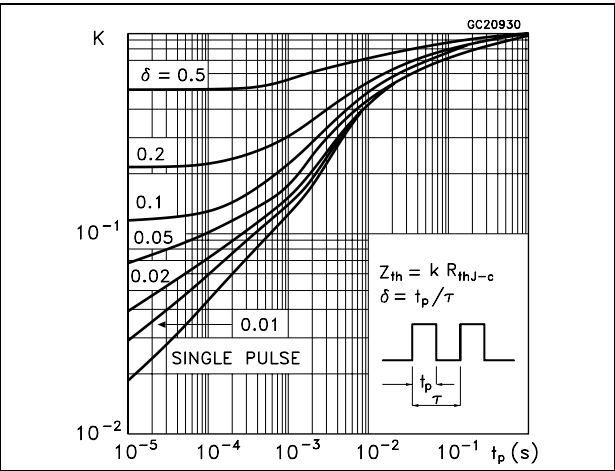


Figure 4. Safe operating area for DPAK, IPAK

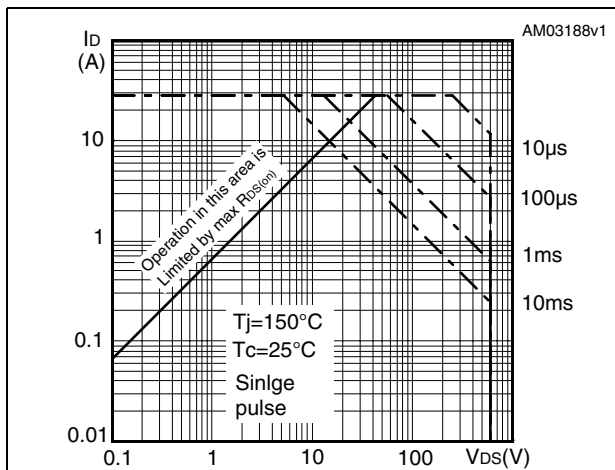


Figure 5. Thermal impedance for DPAK, IPAK

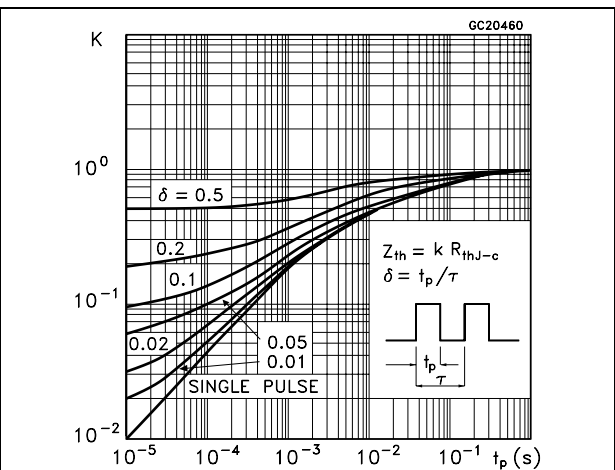


Figure 6. Safe operating area for TO-220FP

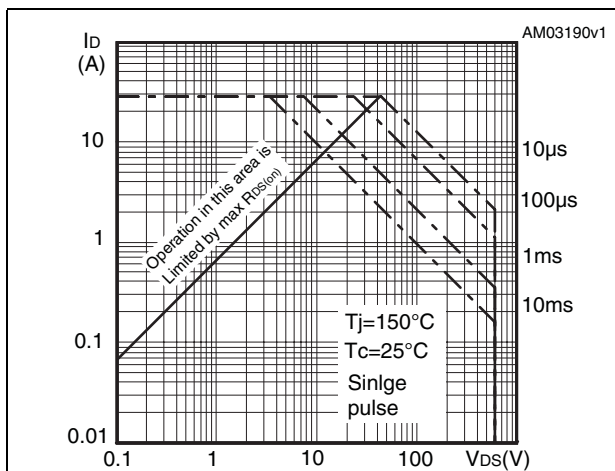


Figure 7. Thermal impedance for TO-220FP

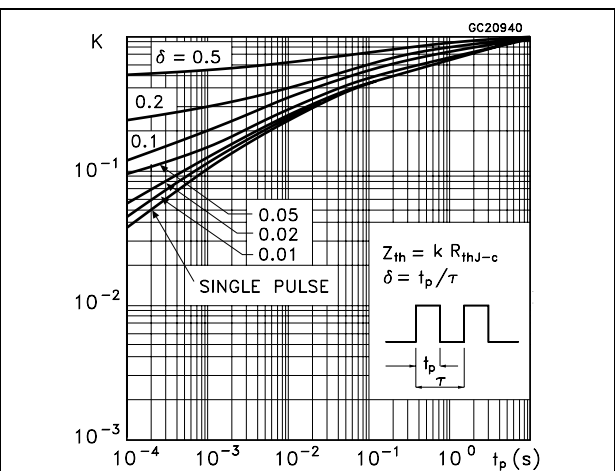


Figure 8. Output characteristics

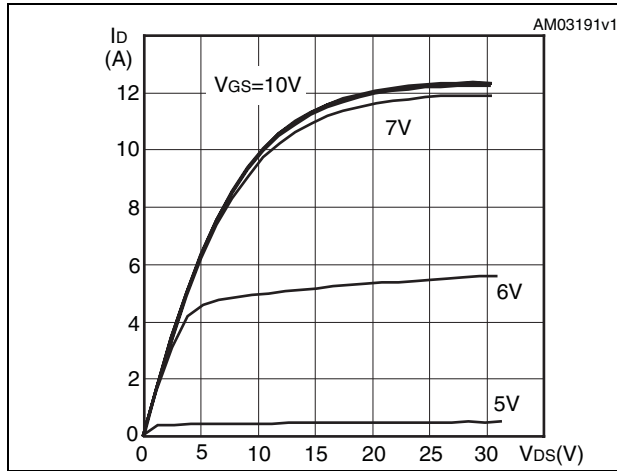


Figure 9. Transfer characteristics

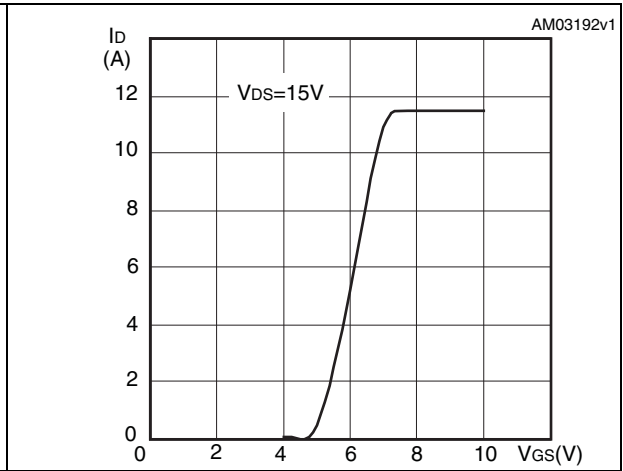


Figure 10. Transconductance

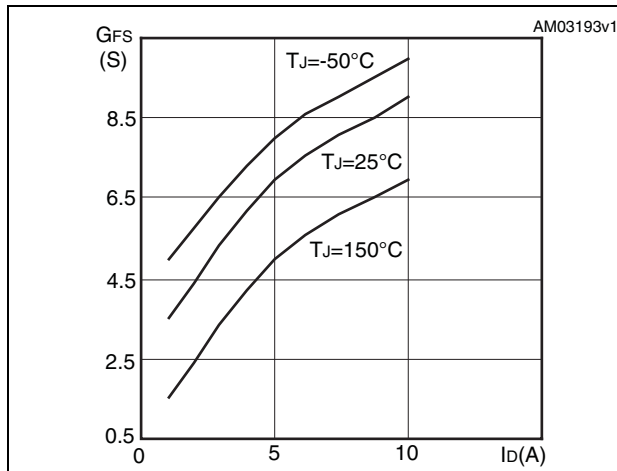


Figure 11. Static-drain source on resistance

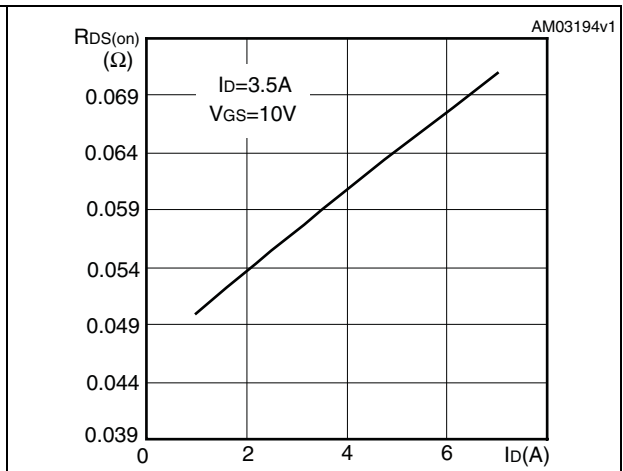


Figure 12. Gate charge vs gate-source voltage Figure 13. Capacitance variations

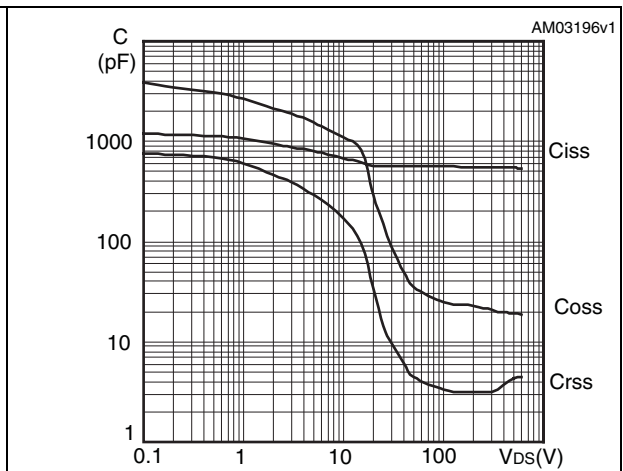
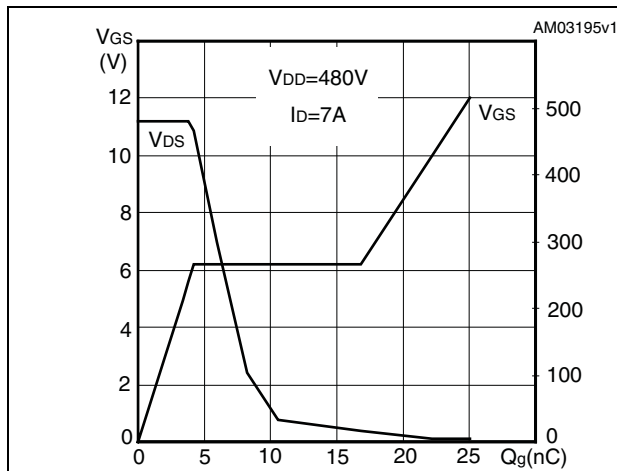


Figure 14. Normalized gate threshold voltage vs temperature

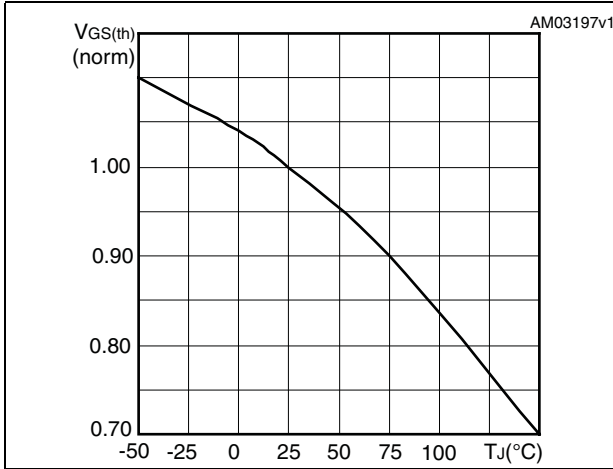


Figure 15. Normalized on resistance vs temperature

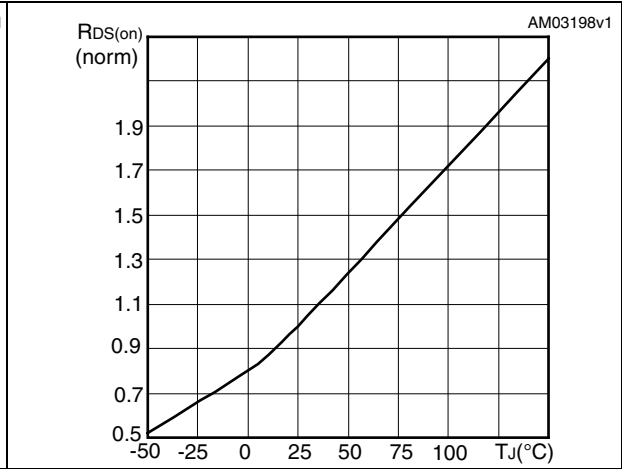


Figure 16. Source-drain diode forward characteristics

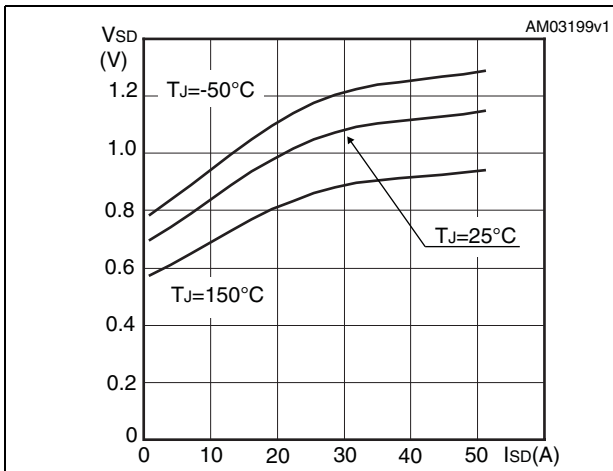
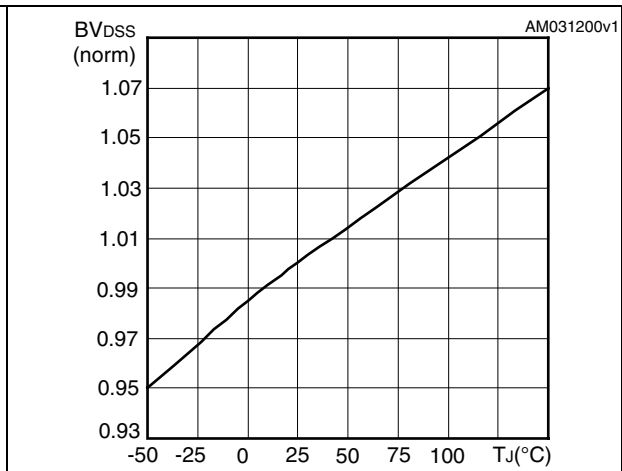


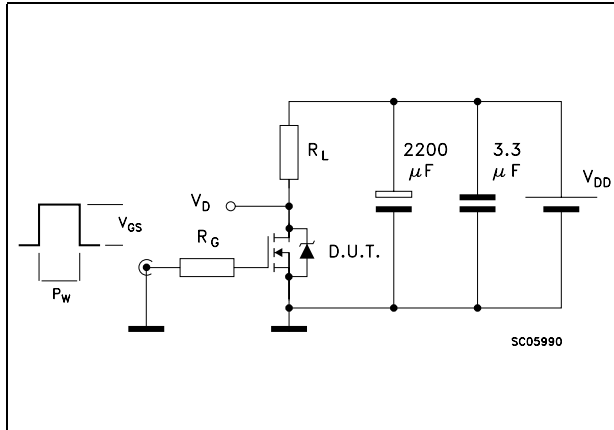
Figure 17. Normalized BV<sub>DSS</sub> vs temperature



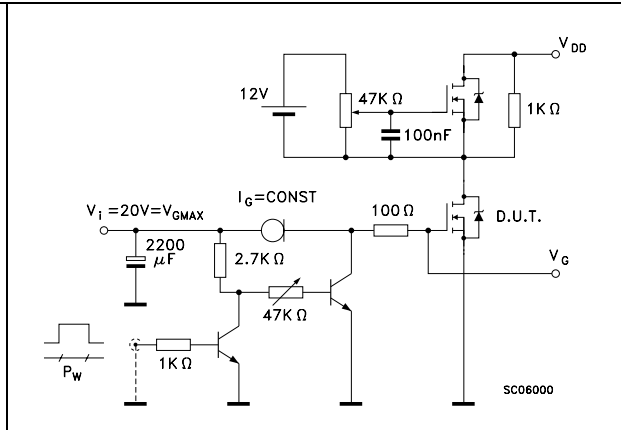


### 3 Test circuits

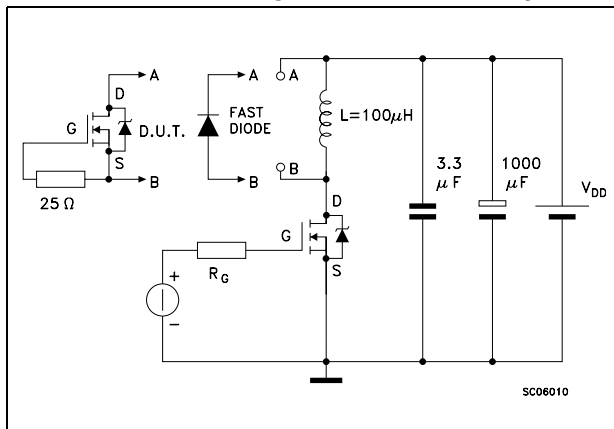
**Figure 18. Switching times test circuit for resistive load**



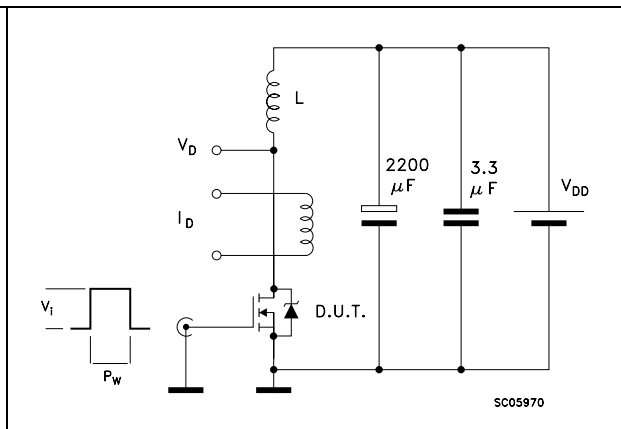
**Figure 19. Gate charge test circuit**



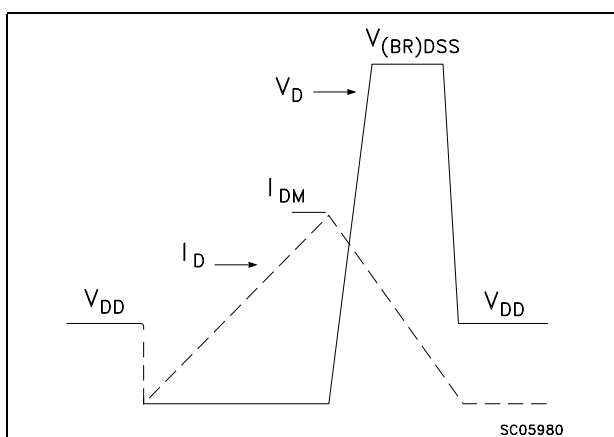
**Figure 20. Test circuit for inductive load switching and diode recovery times**



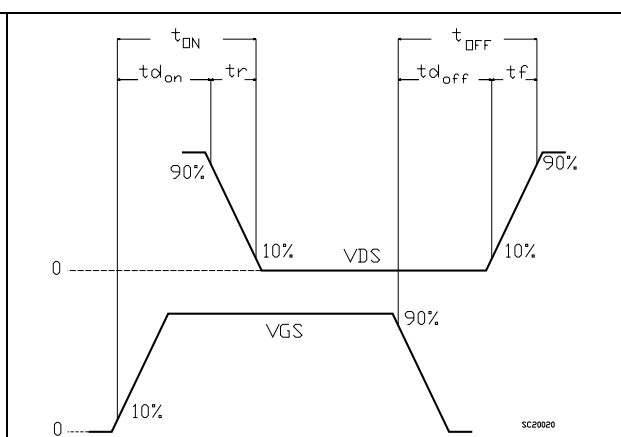
**Figure 21. Unclamped inductive load test circuit**



**Figure 22. Unclamped inductive waveform**



**Figure 23. Switching time waveform**

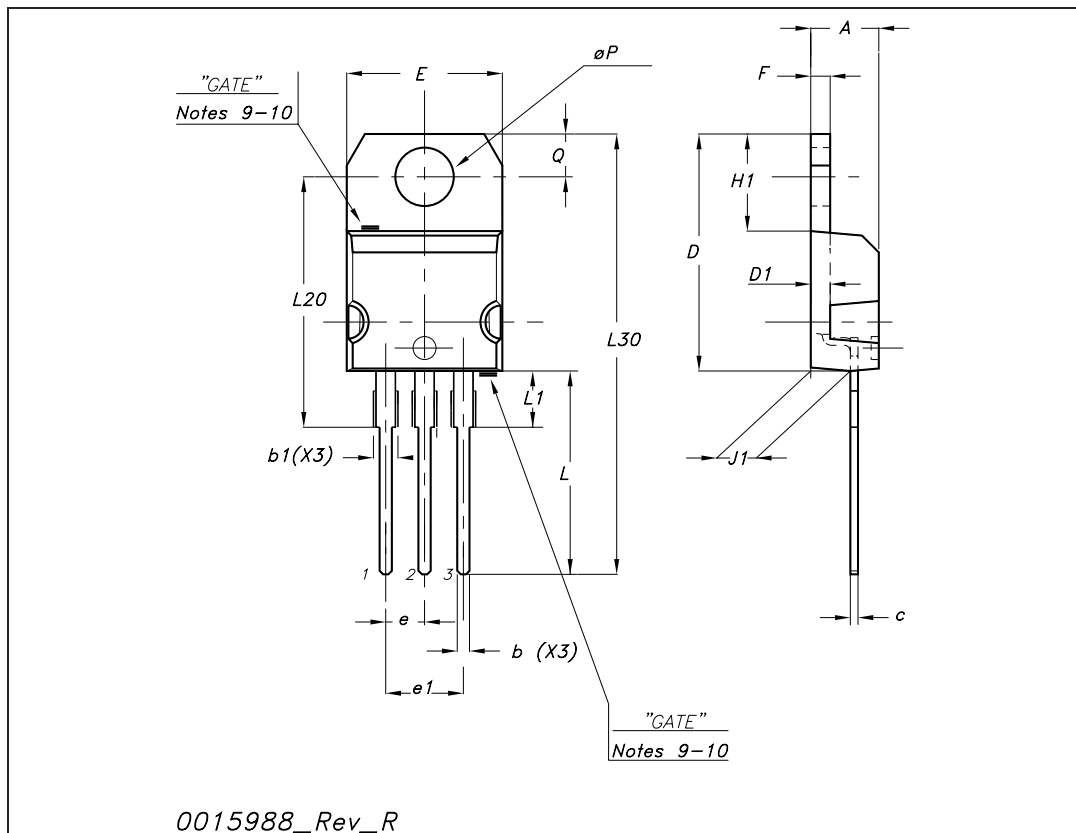


## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.

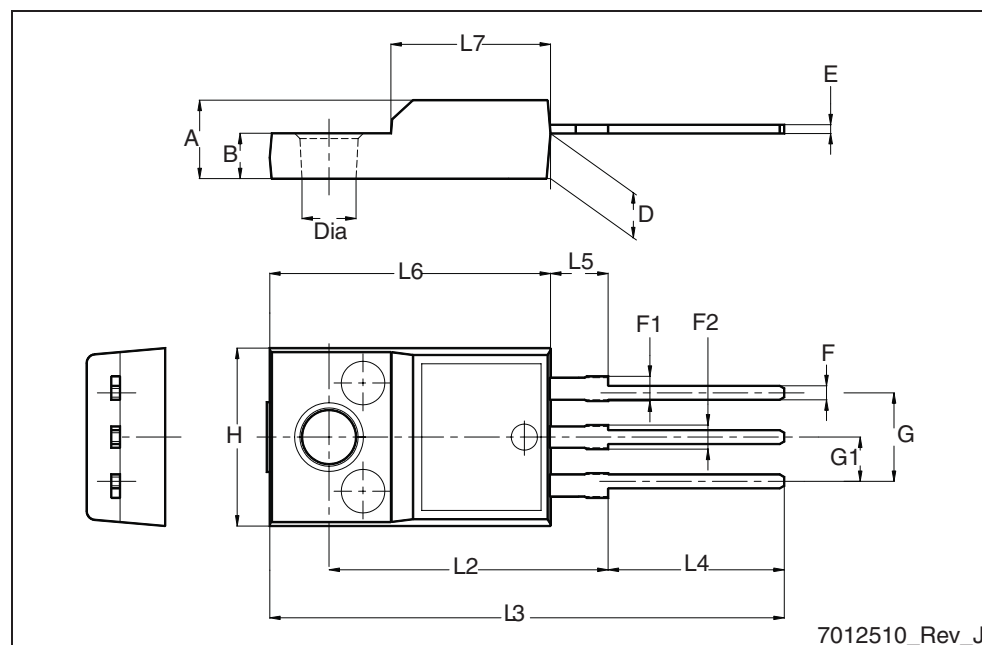
TO-220 mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.48		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
∅P	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



TO-220FP mechanical data

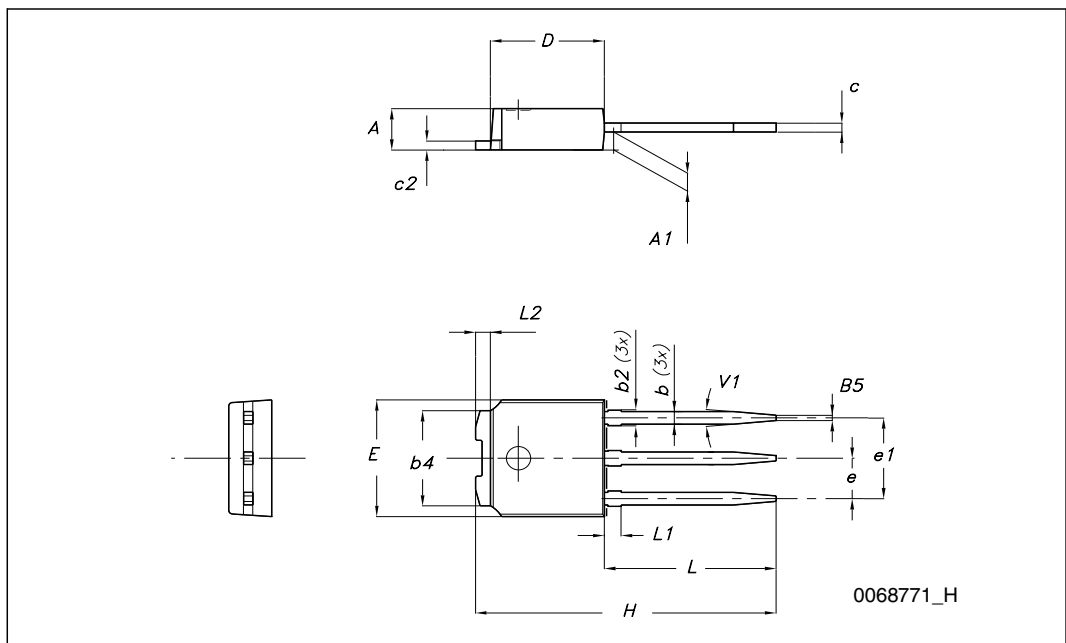
Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.5
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2



7012510\_Rev\_J

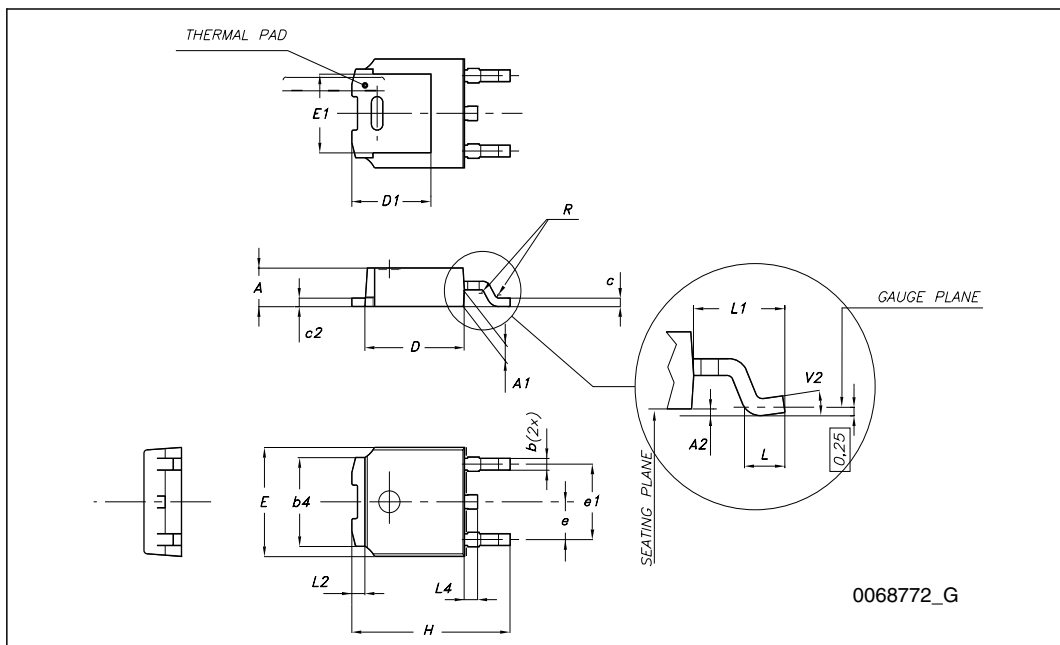
## TO-251 (IPAK) mechanical data

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
e		2.28	
e1	4.40		4.60
H		16.10	
L	9.00		9.40
(L1)	0.80		1.20
L2		0.80	
V1		10°	



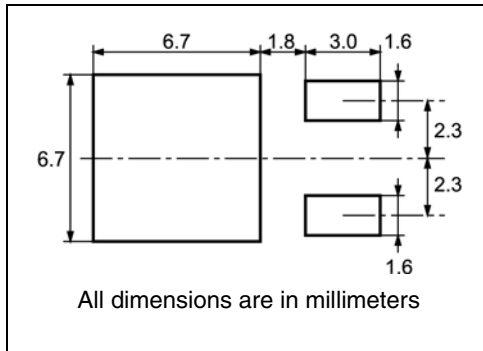
**TO-252 (DPAK) mechanical data**

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0°		8°



# 5 Packaging mechanical data

## DPAK FOOTPRINT



## TAPE AND REEL SHIPMENT

40 mm min. Access hole at slot location

Full radius

Tape slot in core for tape start 2.5mm min. width

G measured at hub

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	16.4	18.4	0.645	0.724
N	50		1.968	
T		22.4		0.881

BASE QTY	BULK QTY
2500	2500

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	6.8	7	0.267	0.275
B0	10.4	10.6	0.409	0.417
B1		12.1		0.476
D	1.5	1.6	0.059	0.063
D1	1.5		0.059	
E	1.65	1.85	0.065	0.073
F	7.4	7.6	0.291	0.299
K0	2.55	2.75	0.100	0.108
P0	3.9	4.1	0.153	0.161
P1	7.9	8.1	0.311	0.319
P2	1.9	2.1	0.075	0.082
R	40		1.574	
W	15.7	16.3	0.618	0.641

For machine ref. only including draft and radii concentric around B0

10 pitches cumulative tolerance on tape +/- 0.2 mm

User Direction of Feed

FEED DIRECTION

Bending radius R min.

## 6 Revision history

**Table 9. Document revision history**

Date	Revision	Changes
09-Feb-2009	1	First release



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